ABSTRACT

An integrated circuit having copper interconnecting metallization (311, 312) protected by a first, inorganic overcoat layer (320), portions of the metallization exposed in windows (301, 302) opened through the thickness of the first overcoat layer. A patterned conductive barrier layer (330) is positioned on the exposed portion of the copper metallization and on portions of the first overcoat layer surrounding the window. A bondable metal layer (350, 351) is positioned on the barrier layer; the thickness of this bondable layer is suitable for wire bonding. A second, organic overcoat layer (360) is surrounding the window so that the surface (360a) of this second overcoat layer at the edge of the window is at or above the surface (350a) of the bondable layer. The second overcoat layer may be spaced (370) from the edge of the bondable metal layer.